

Description

The AU2421D3 is a 24V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU2421D3 complies with the IEC 61000-4-2 (ESD) with ± 25 kV air and ± 20 kV contact discharge. It is assembled into a SOD-323 leadfree package. The small size and high ESD surge protection make AU2421D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 24V
- Low clamping voltage
- 2-Pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ± 25 kV
 - Contact discharge: ± 20 kV
 - IEC61000-4-5 (Lightning) 3.5A (8/20 μ s)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

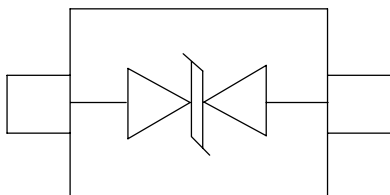
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

Marking Information



24E = Device Marking Code

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AU2421D3	10,000/Tape & Reel	7 inch

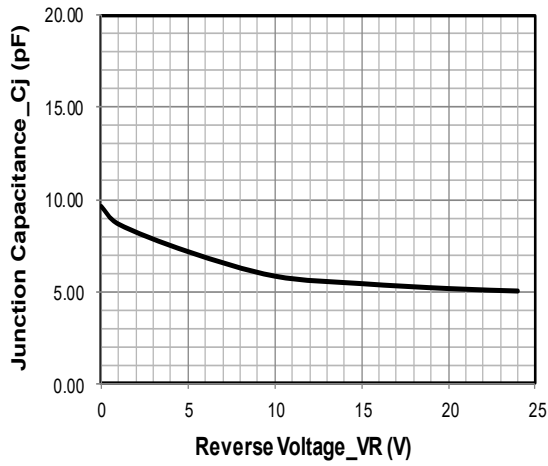
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	180	W
Peak Pulse Current (8/20 μs)	Ipp	3.5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	± 25 ± 20	kV
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

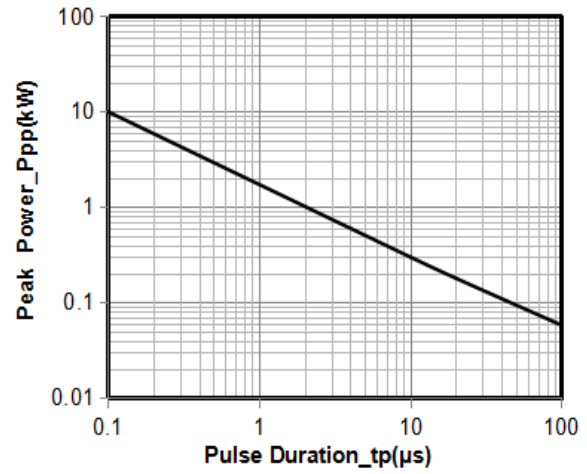
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27	31		V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	VRWM = 24V
Clamping Voltage	VC		45	60	V	I _{PP} = 3.5A (8 x 20 μs pulse)
Junction Capacitance	CJ		10		pF	VR = 0V, f = 1MHz

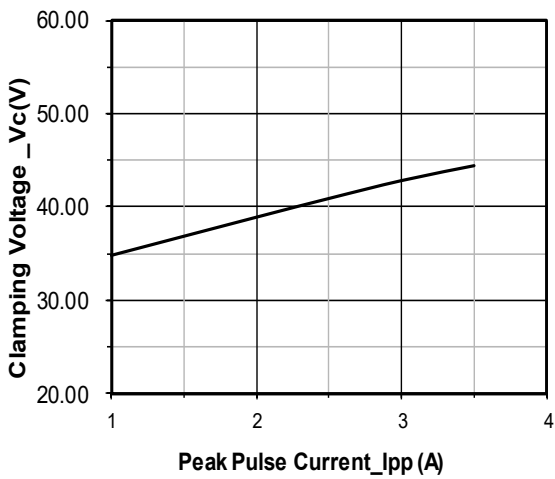
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



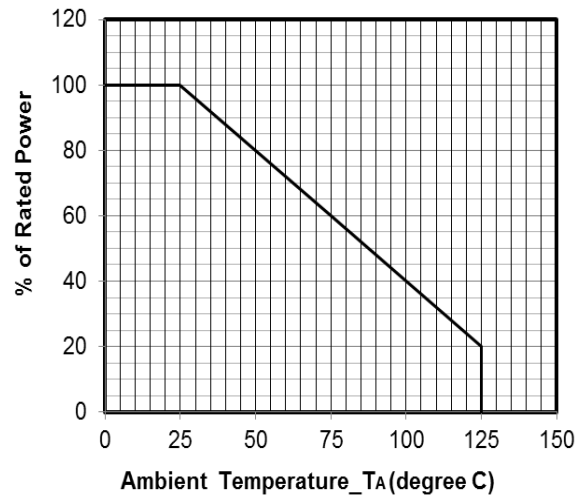
Junction Capacitance vs. Reverse Voltage



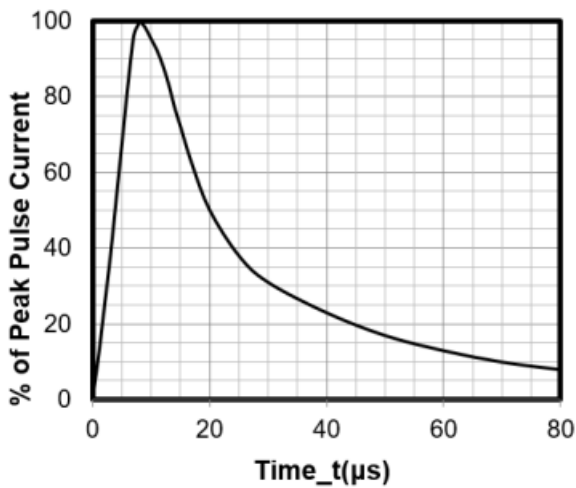
Peak Pulse Power vs. Pulse Time



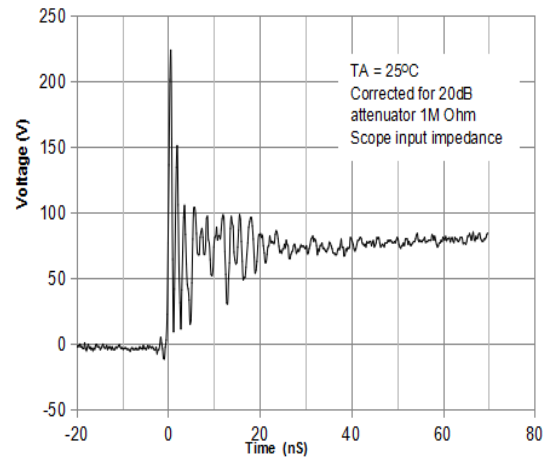
Clamping Voltage vs. Peak Pulse Current



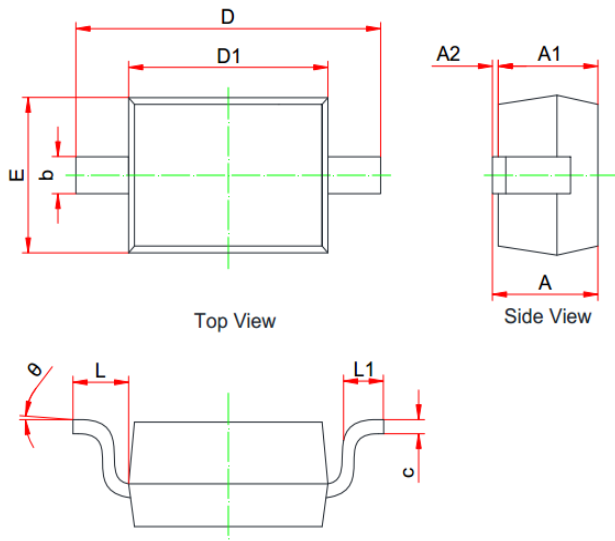
Power Derating Curve



8 X 20 μs Pulse Waveform



**ESD Clamping Voltage
8 kV Contact per IEC61000-4-2**

SOD-323 Package Outline Drawing


	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern

Unit: mm
Contact Information

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